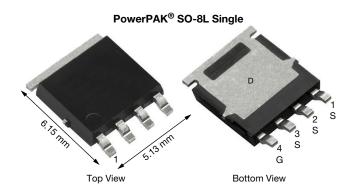


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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	60		
$R_{DS(on)}$ (Ω) at $V_{GS} = 10 \text{ V}$	0.0125		
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0160		
I _D (A)	30		
Configuration	Single		
Package	PowerPAK SO-8L		

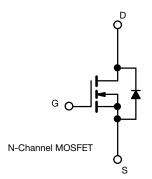
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ABSOLUTE MAXIMUM RATING	(1) = 25 O, unics				
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V _{GS} ± 20		v	
Continuous Drain Current	T _C = 25 °C ^a	1	30		
	T _C = 125 °C	- I _D	24.6		
Continuous Source Current (Diode Conduction) ^a		Is	30	Α	
Pulsed Drain Current b		I _{DM}	84	l	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	23]	
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	26	mJ	
Maximum Power Dissipation b	T _C = 25 °C	D_	45	W	
	T _C = 125 °C	P _D	15		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	
Soldering Recommendations (Peak Temperature) d, e		<u> </u>	260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount c	R_{thJA}	70	°C/W	
Junction-to-Case (Drain)		R_{thJC}	3.3	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



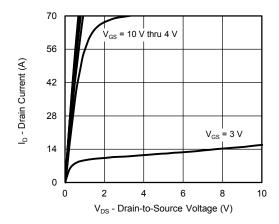
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$		1.5	2.0	2.5	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current		V _{GS} = 0 V	V _{DS} = 60 V	-	-	1	μΑ
	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V	I _D = 8 A	-	0.0101	0.0125	Ω
		V _{GS} = 4.5 V	I _D = 6 A	-	0.0131	0.0160	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 8 A, T _J = 125 °C	-	-	0.0202	
		V _{GS} = 10 V	I _D = 8 A, T _J = 175 °C	-	-	0.0249	
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 8 A		-	46	-	S
Dynamic ^b					•		
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	1195	1600	pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		-	506	660	
Reverse Transfer Capacitance	C _{rss}			-	31	45	
Total Gate Charge ^c	Qg			-	18	30	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 4 \text{ A}$	-	3.4	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	2.5	-	
Gate Resistance	Rg	f = 1 MHz		0.2	0.47	0.8	Ω
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 30 \text{ V}, \text{ R}_L = 7.5 \Omega$ $I_D \cong 4 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	9	15	ns
Rise Time ^c	t _r			-	5	10	
Turn-Off Delay Time ^c	t _{d(off)}			-	21	35	
Fall Time ^c	t _f			-	5	10	
Source-Drain Diode Ratings and Chara	acteristics ^b				•		
Pulsed Current ^a	I _{SM}			-	-	84	Α
Forward Voltage	V_{SD}	I _F = 8 A, V _{GS} = 0		-	0.82	1.2	V

Notes

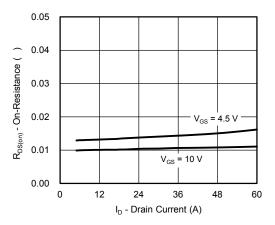
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

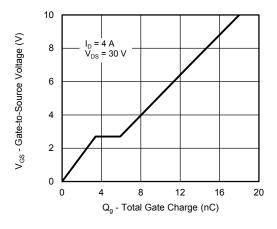




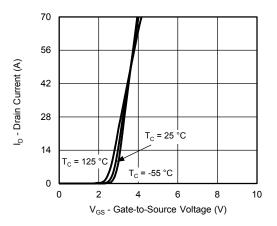
Output Characteristics



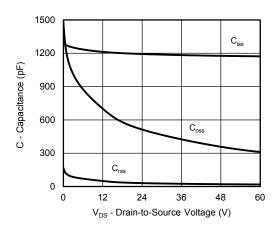
On-Resistance vs. Drain Current



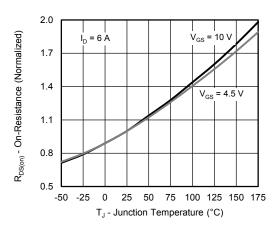
Gate Charge



Transfer Characteristics

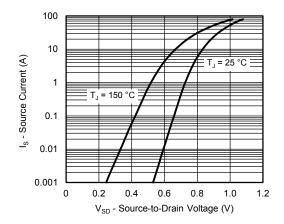


Capacitance

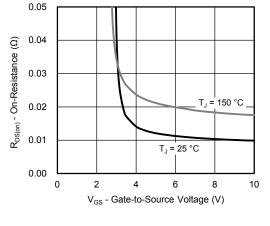


On-Resistance vs. Junction Temperature

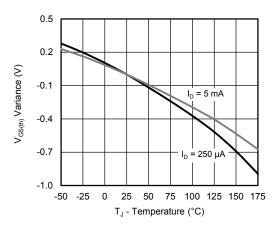




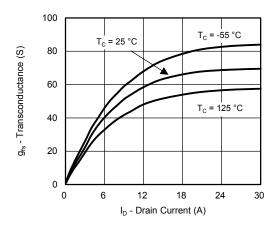
Source Drain Diode Forward Voltage



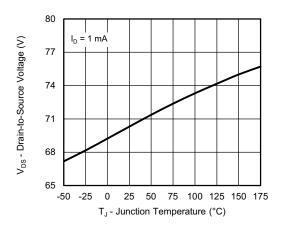
On-Resistance vs. Gate-to Source Voltage



Threshold Voltage

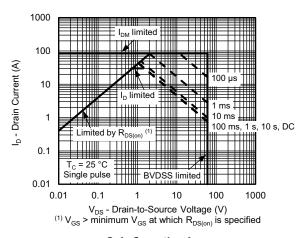


Transconductance

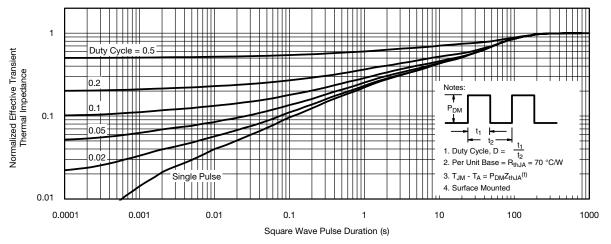


Drain Source Breakdown vs. Junction Temperature





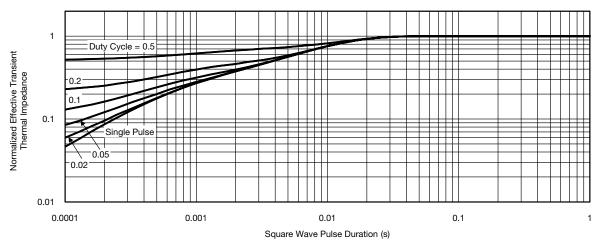
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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